



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant : Chang-Rong WU et al. Confirmation No: 9777  
Appl. No. : 10/810,804  
Filed : March 29, 2004  
Title : Method And Composite Hard Mask For Forming Deep Trenches In A Semiconductor Substrate  
  
TC/A.U. : 2823  
Examiner : F.L. Toledo  
  
Docket No.: WUCH3037/REF  
Customer No: 23364

**AMENDMENT**

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of September 13, 2005, in connection with the above-identified application. This response is timely filed.

Please amend the application as follows:

Amendments to the specification begin on page 2 of this paper.

Amendments to the claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks begin on page 5 of this paper.